

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-20 (Cancelled)

Claim 21. (Currently amended) A ferroelectric memory device comprising:

a first interlayer insulating layer formed on a semiconductor substrate;

a buried contact structure electrically connected to the substrate through a first contact hole extending through the first interlayer insulating layer, the buried contact structure formed on the first interlayer insulating layer;

B1 a blocking layer formed on the buried contact structure and the first interlayer insulating layer;

a second interlayer insulating layer formed on the blocking layer; and

a ferroelectric capacitor that fills a second contact hole and connects to the buried contact structure through the second contact hole that penetrates the second interlayer insulating layer and the blocking layer, the ferroelectric capacitor being formed on the second interlayer insulating layer.

Claim 22. (Currently amended) The ferroelectric memory device according to claim 21, wherein the blocking layer comprises a material chosen from the group consisting of silicon oxynitride (SiON), silicon nitride (SiN), or and aluminum oxide ~~to prevent oxygen diffusion~~.

Claim 23. (original) The ferroelectric memory device according to claim 21, wherein a diameter of the second contact hole is larger than a diameter of the first contact hole.

Claim 24. (original) The ferroelectric memory device according to claim 21, wherein the buried contact structure is made of tungsten (W).
